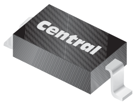
CMDD2004

SURFACE MOUNT
HIGH VOLTAGE
SILICON SWITCHING DIODE

SUPERmini™



SOD-323 CASE

Central™ Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The Central Semiconductor CMDD2004 is a high voltage silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: C24

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	250	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Peak Forward Surge Current, tp=1.0μs	I_{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0s	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +175	°C
Thermal Resistance	Θ_{JA}	600	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNIT**
I_R	V_R=240V		100	nA
I_R	V_R=240V, T_A=150°C		100	μA
BV_R	I_R=100μA	300		V
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1.0MHz		5.0	pF
t_{rr}	I_F=I_R=30mA, I_{rr}=3.0mA, R_L=100Ω		50	ns

R6 (24-June 2011)

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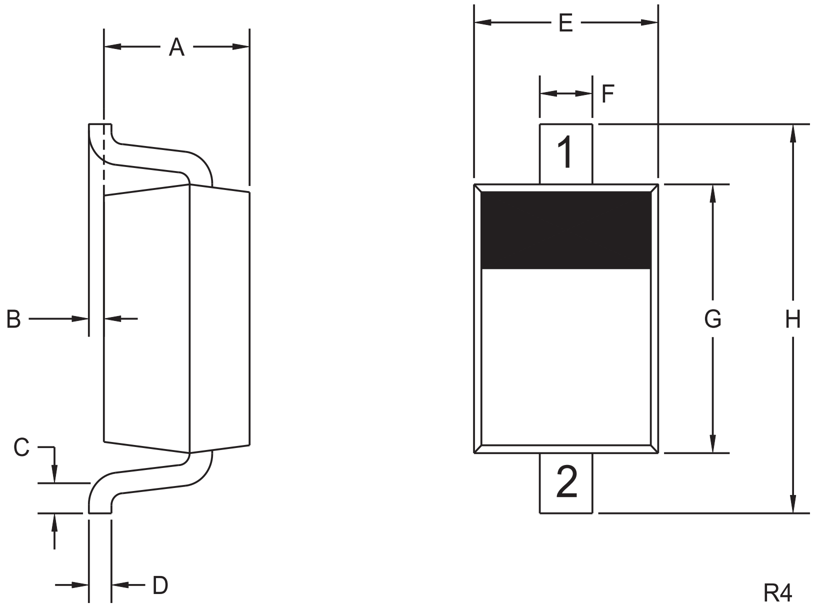
SOD-323 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Cathode
2) Anode

MARKING CODE: C24

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R6 (24-June 2011)